NSN 5961-01-156-5796

A110a0

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-156-5796 **Inclosure Material:** Plastic **Overall Length:** 0.650 inches **Overall Height:** 0.190 inches **Overall Width:** 0.420 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-220 **Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 0.8 gate trigger voltage, dc and 200.0 repetitive peak reverse voltage, peak total value, gate terminal open-circuited **Current Rating Per Characteristic:** 4.00 amperes forward current, total rms horsepower metric and 35.00 amperes forward current, total rms watts and 0.20 milliamperes forward current, total rms preset **Special Features:** Junction pattern arrangement: pn **Terminal Type And Quantity:** 1 tab, solder lug and 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: